# LAPT 2SC3264

#### Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1295)

## Application: Audio and General Purpose

## Absolute maximum ratings (Ta=25°C)

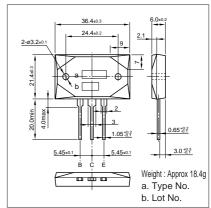
Symbol	2SC3264	Unit
Vсво	230	V
VCEO	230	V
VEBO	5	V
Ic	17	А
Ів	5	А
Pc	200(Tc=25°C)	W
Tj	150	°C
Tstg	-55 to +150	°C

## Electrical Characteristics

	iai aotoriotioo	(1a=25 0)		
Symbol	Conditions	2SC3264	Unit	
Ісво	Vcb=230V	100max	μА	
<b>І</b> ЕВО	VEB=5V	100max		
V(BR)CEO	Ic=25mA	230min	V	
hfe	Vce=4V, Ic=5A	50min*		
Vce(sat)	Ic=5A, IB=0.5A	2.0max	V	
fT	Vce=12V, Ie=-2A	60typ	MHz	
Сов	Vcb=10V, f=1MHz	250typ	pF	

\*hfe Rank  $\overline{O}$ (50 to 100), Y(70 to 140)

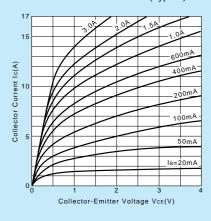
## **External Dimensions MT-200**



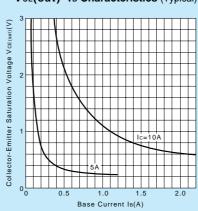
#### ■Typical Switching Characteristics (Common Emitter)

Vcc (V)	Rι (Ω)	Ic (A)	V <sub>BB1</sub> (V)	V <sub>BB2</sub> (V)	I <sub>B1</sub> (A)	IB2 (A)	ton (µs)	tstg (µs)	tf (µs)
60	12	5	10	-5	0.5	-0.5	0.30typ	2.40typ	0.50typ

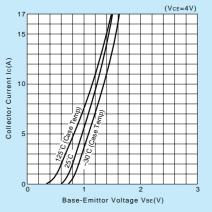
## Ic-VcE Characteristics (Typical)



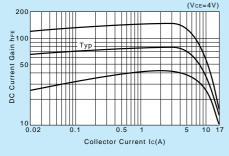
VcE(sat)-IB Characteristics (Typical)



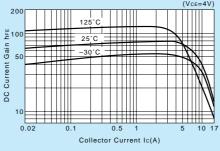
Ic-VBE Temperature Characteristics (Typical)



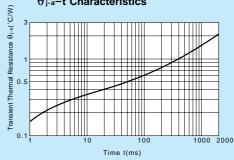
hfe-Ic Characteristics (Typical)



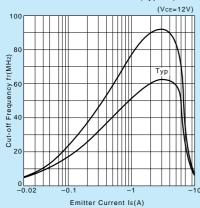
hfe-Ic Temperature Characteristics (Typical)



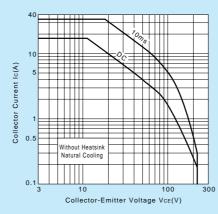
θ<sub>j-a</sub>-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

